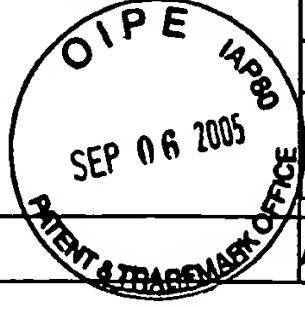


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		Application Number	09/945,507
		Filing Date	August 30, 2001
		First Named Inventor	Forbes, Leonard
		Group Art Unit	2824
		Examiner Name	Dinh, Son
Sheet 1 of 2		Attorney Docket No: 1303.014US1	



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